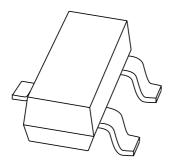
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT54 seriesSchottky barrier (double) diodes

Product data sheet Supersedes data of 2001 Oct 12 2002 Mar 04



Schottky barrier (double) diodes

BAT54 series

FEATURES

- Low forward voltage
- · Guard ring protected
- · Small plastic SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diodes encapsulated in a SOT23 small plastic SMD package. Single diodes and double diodes with different pinning are available.

MARKING

TYPE NUMBER	MARKING CODE(1)
BAT54	L4*
BAT54A	L42 or *V3
BAT54C	L43 or *W1
BAT54S	L44 or *V4

Note

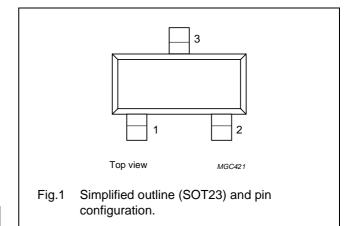
1. * = p: Made in Hong Kong.

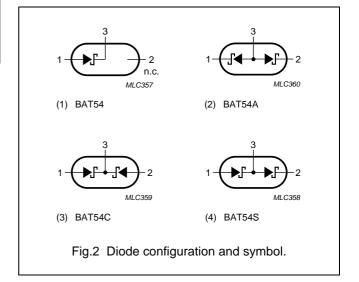
* = t : Made in Malaysia.

* = W: Made in China.

PINNING

PIN	DESCRIPTION						
FIN	BAT54	BAT54A	BAT54C	BAT54S			
1	а	k ₁	a ₁	a ₁			
2	n.c.	k ₂	a ₂	k ₂			
3	k	a ₁ , a ₂	k ₁ , k ₂	k ₁ , a ₂			





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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode		·			
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s; } \delta \le 0.5$	-	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	-	600	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	125	°C
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	230	mW

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	500	K/W
1	ambient			

Note

1. Refer to SOT23 standard mounting conditions.

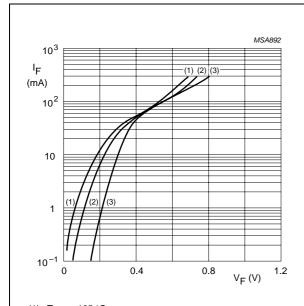
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V _F	forward voltage	see Fig.3		
		$I_F = 0.1 \text{ mA}$	240	mV
		I _F = 1 mA	320	mV
		I _F = 10 mA	400	mV
		I _F = 30 mA	500	mV
		I _F = 100 mA	800	mV
I _R	reverse current	V _R = 25 V; see Fig.4	2	μΑ
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.6	5	ns
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}; \text{ see Fig.5}$	10	pF

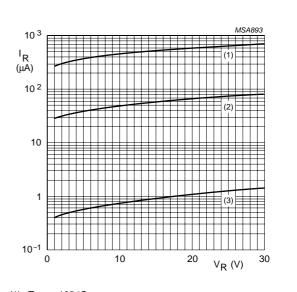
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BAT54 series



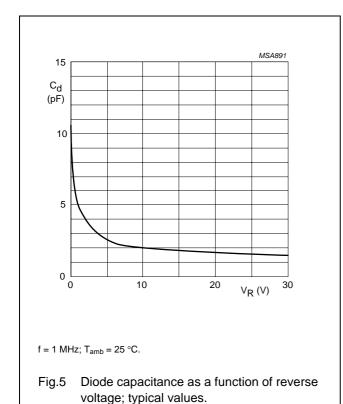
- (1) $T_{amb} = 125 \,^{\circ}C$.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

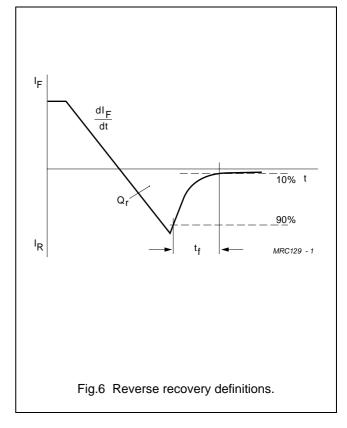
Fig.3 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig.4 Reverse current as a function of reverse voltage; typical values.





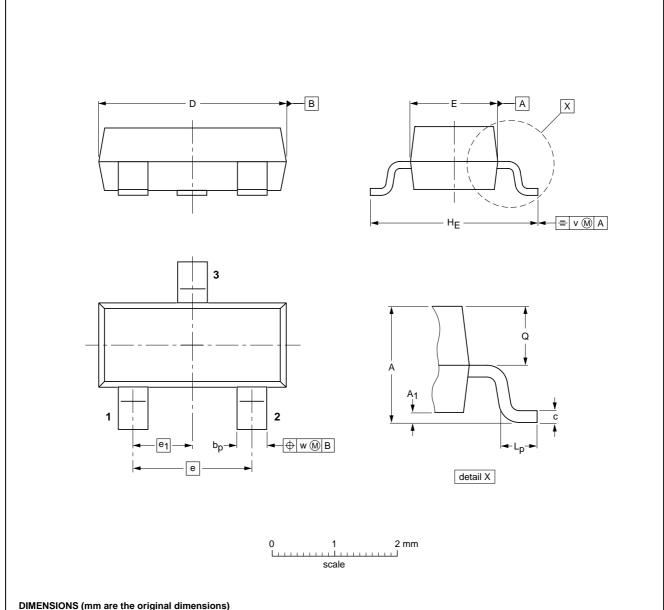
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



UNIT	A	A ₁ max.	bp	С	D	E	е	e ₁	HE	L _p	Q	٧	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				97-02-28 99-09-13

2002 Mar 04 5

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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Printed in The Netherlands 613514/04/pp7 Date of release: 2002 Mar 04 Document order number: 9397 750 09408

